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Correction: First-principles calculations of interfacial thermal transport properties between SiC/Si substrates and compounds of boron with selected group V elements

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Correction for 'First-principles calculations of interfacial thermal transport properties between SiC/Si substrates and compounds of boron with selected group V elements' by Zhehao Sun et al., *Phys. Chem. Chem. Phys.*, 2019, 21, 6011–6020, <https://doi.org/10.1039/C8CP07516F>.

Fig. 7 was shown incorrectly, the correct Fig. 7 is shown herein.

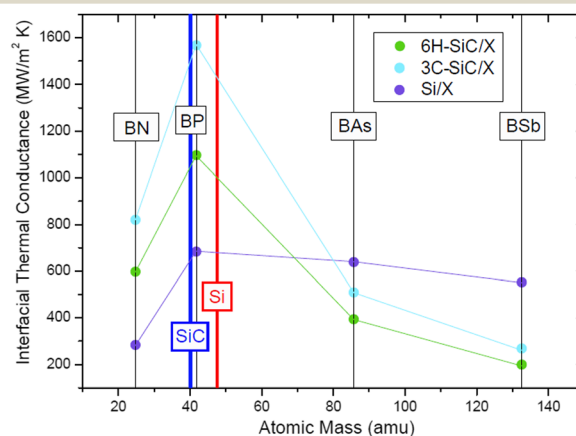


Fig. 7 Interfacial thermal conductance as a function of atomic masses. The black straight line is atomic mass of compounds of boron with group V elements. The blue and red straight lines represent the atomic mass of SiC and Si, respectively. The circles are the calculated values of interfacial thermal conductance.

The Royal Society of Chemistry apologises for these errors and any consequent inconvenience to authors and readers.

